

2N6193U3

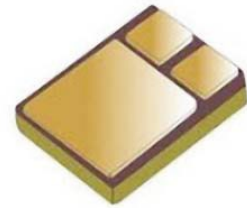


PNP Switching Silicon Transistor

Rev. V5

Features

- JAN, JANTX, JANTXV, JANS and JANSR Qualified to MIL-PRF-19500/561
- JEDEC Registered 2N6193
- Lightweight & Low Power
- Ideal for Space, Military, and Other High Reliability Applications
- Surface Mount U3 (TO-276AA) Package



Electrical Characteristics ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	$I_C = -50 \text{ mA dc}$	$V_{(BR)CEO}$	V dc	-100	—
Collector - Emitter Cutoff Current	$V_{CE} = -100 \text{ V dc}$	I_{CEO}	$\mu\text{A dc}$	—	-100
Collector - Emitter Cutoff Current	$V_{BE} = +1.5 \text{ Vdc}; V_{CE} = -90 \text{ V dc}$	I_{CEX1}	$\mu\text{A dc}$	—	-10
Collector - Base Cutoff Current	$V_{CB} = -100 \text{ V dc}$	I_{CBO}	$\mu\text{A dc}$	—	-10
Emitter - Base Cutoff Current	$V_{EB} = -6.0 \text{ V dc}$	I_{EBO}	$\mu\text{A dc}$	—	-100
Forward - Current Transfer Ratio	$V_{CE} = -2.0 \text{ V dc}; I_C = -0.5 \text{ A dc}$ $V_{CE} = -2.0 \text{ V dc}; I_C = -2.0 \text{ A dc}$ $V_{CE} = -2.0 \text{ V dc}; I_C = -5.0 \text{ A dc}$	h_{FE}	-	60 60 40	240
Collector - Emitter Saturation Voltage	$I_C = -2.0 \text{ A dc}; I_B = -0.2 \text{ A dc}$ $I_C = -5.0 \text{ A dc}; I_B = -0.5 \text{ A dc}$	$V_{CE(SAT)1}$ $V_{CE(SAT)2}$	V dc	—	-0.7 -1.2
Emitter - Base Saturation Voltage	$I_C = -2.0 \text{ A dc}; I_B = -0.2 \text{ A dc}$ $I_C = -5.0 \text{ A dc}; I_B = -0.5 \text{ A dc}$	$V_{BE(SAT)1}$ $V_{BE(SAT)2}$	V dc	—	-1.2 -1.8
Collector - Emitter Cutoff Current	$T_A = +150^\circ\text{C}$ $V_{CE} = -90 \text{ V dc}; V_{BE} = +1.5 \text{ Vdc}$	I_{CEX2}	$\mu\text{A dc}$	—	-15
Forward - Current Transfer Ratio	$T_A = -55^\circ\text{C}$ $V_{CE} = -2.0 \text{ V dc}; I_C = -2.0 \text{ A dc}$	h_{FE4}	-	12	
Dynamic Characteristics					
Small-Signal Short-Circuit Forward - Current Transfer Ratio	$V_{CE} = -10.0 \text{ V dc}; I_C = -0.5 \text{ A dc}; f = 10 \text{ MHz}$	$ h_{fe} $	-	3	15
Output Capacitance	$V_{CB} = -10 \text{ V dc}; I_E = 0; 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	C_{obo}	pF	—	300
Input Capacitance	$V_{BE} = -2 \text{ V dc}; I_C = 0; 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	C_{ibo}	pF	—	1250
Switching Characteristics					
Delay Time	See figure 11 of MIL-PRF-19500/561	t_d	ns	—	100
Rise Time	See figure 11 of MIL-PRF-19500/561	t_r	ns	—	100
Storage Time	See figure 12 of MIL-PRF-19500/561	t_s	μs	—	2.0
Fall Time	See figure 12 of MIL-PRF-19500/561	t_f	ns	—	200

Absolute Maximum Ratings ($T_A = +25^\circ\text{C}$ unless otherwise noted)

Ratings	Symbol	Value
Collector - Emitter Voltage	V_{CEO}	-100 V dc
Collector - Base Voltage	V_{CBO}	-100 V dc
Emitter - Base Voltage	V_{EBO}	-6.0 V dc
Base Current	I_B	-1.0 A dc
Collector Current	I_C	-5.0 A dc
Total Power Dissipation @ $T_A = +25^\circ\text{C}$ ⁽¹⁾ @ $T_C = +25^\circ\text{C}$ ⁽²⁾	P_T	1.0 W 100 W
Operating & Storage Temperature Range	T_J, T_{STG}	-65°C to $+200^\circ\text{C}$

(1) See figure 6 of MIL-PRF-19500/561

(2) See figure 7 and 8 of MIL-PRF-19500/561

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.75°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	175°C/W

Safe Operating Area

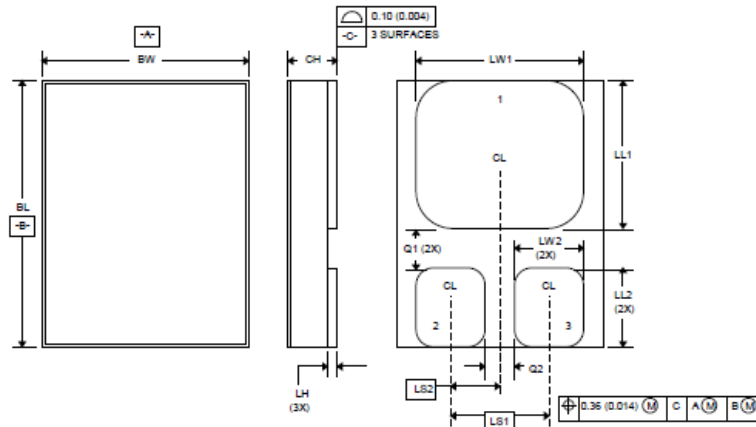
DC Tests:	$T_C = +25^\circ\text{C}; t \geq 0.5 \text{ s}; 1 \text{ Cycle}$
Test 1:	$V_{CE} = -2.0 \text{ V dc}; I_C = -5.0 \text{ A dc}$
Test 2:	$V_{CE} = -90 \text{ V dc}; I_C = -55 \text{ mA dc}$

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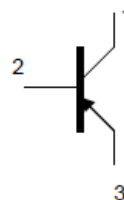
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Outline Drawing (U3)



Ltr	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.395	.405	10.04	10.28
BW	.291	.301	7.40	7.64
CH	.1085	.1205	2.76	3.06
LH	.010	.020	0.25	0.51
LW1	.281	.291	7.14	7.39
LW2	.090	.100	2.29	2.54
LL1	.220	.230	5.59	5.84
LL2	.115	.125	2.93	3.17
LS1	.150 BSC		3.81 BSC	
LS2	.075 BSC		1.91 BSC	
Q1	.030		0.762	
Q2	.030		0.762	

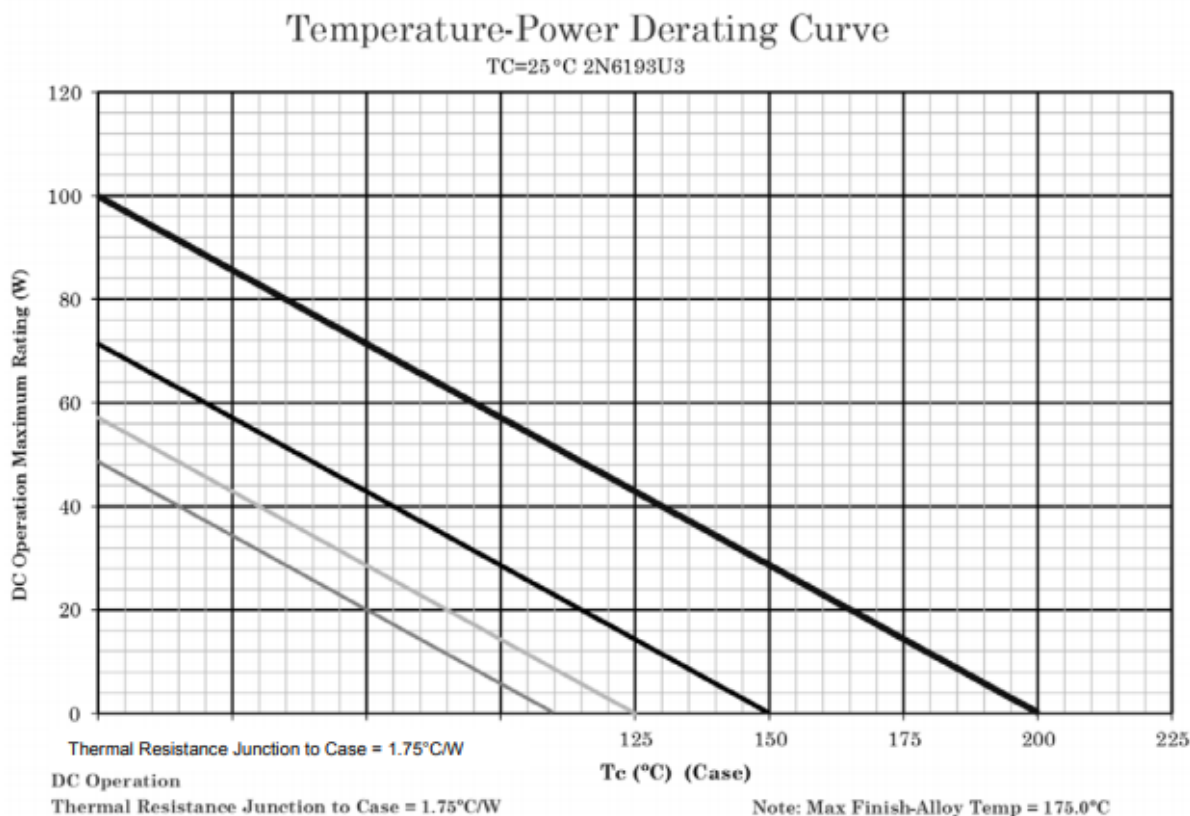
SCHEMATIC



NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.
4. Terminal 1 - collector, terminal 2 - base, terminal 3 - emitter.

FIGURE 5. Physical dimensions and configuration 2N6193U3.

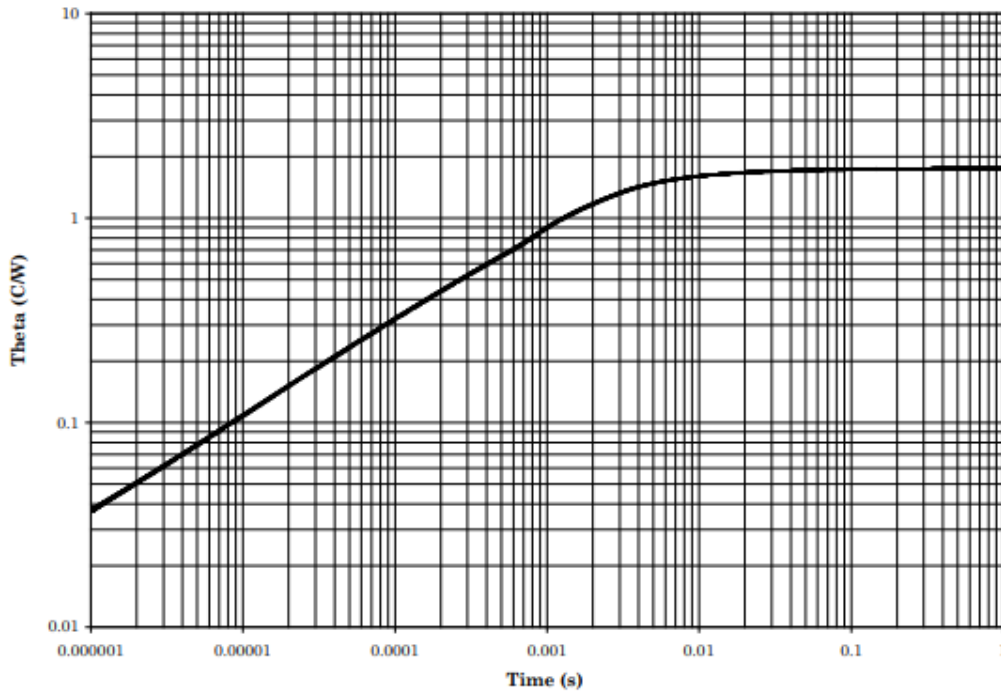


NOTES:

1. Maximum theoretical derate design curve. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperature ($T_J \leq 200^\circ\text{C}$) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq 150^\circ\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curve chosen at $T_J \leq 125^\circ\text{C}$, and 110°C to show power rating where most users want to limit T_J in their application.

* FIGURE 8. Temperature-power derating for 2N6193U3 $R_{\theta JC}$ (U3 package).

Maximum Thermal Impedance



Solder mounted to copper heatsink at $T_C = +25^\circ\text{C}$ thermal resistance = 1.75°C/W , $P_{\text{diss}} = 100\text{W}$.

FIGURE 10. Thermal impedance graph ($R_{\theta\text{JC}}$) for 2N6193U3 (U3).

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